

SEMICONDUCTOR COMPONENT AND METHOD OF MANUFACTURING SAME

ABSTRACT OF THE DISCLOSURE

5 In one embodiment of the invention, a semiconductor component includes a semiconductor substrate (110), a first dielectric layer (120) above the semiconductor substrate, a first ohmic contact region (410) and a second ohmic contact region (420) above the semiconductor substrate, a gate electrode (1120) above the semiconductor substrate and between the first ohmic contact region and the second ohmic contact region, a field plate (210) above the first dielectric layer and between the gate electrode and the second ohmic contact region, a
10 second dielectric layer (310) above the field plate, the first dielectric layer, the first ohmic contact region, and the second ohmic contact region, and a third dielectric layer (910) between the gate electrode and the field plate and not located above the gate electrode or the field plate.